



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

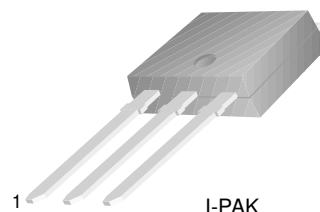


KSC3233

KSC3233

High Speed Switching

- Low Collector-Emitter Saturation Voltage
- High speed Switching : $t_F=1\mu s$ (Max.) @ $I_C=0.8A$
- Collector-Emitter Voltage : $V_{CEO}=400V$
- Lead formed for Surface Mount Applications (D-PAK, " -D " Suffix)



I-PAK
1. Base 2. Collector 3. Emitter

NPN Triple Diffused Planar Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current	2	A
I_B	Base Current	0.5	A
P_C	Collector Dissipation ($T_C=25^\circ C$)	20	W
P_C	Collector Dissipation ($T_a=25^\circ C$)	1	W
T_J	Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature	- 55 ~ 150	$^\circ C$

Electrical Characteristics $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV_{CEO}	Collector-Base Breakdown Voltage	$I_C = 1mA, I_E = 0$	500		V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 10mA, I_B = 0$	400		V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 400V, I_E = 0$		100	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 7V, I_C = 0$		1	mA
h_{FE1} h_{FE2}	DC Current Gain	$V_{CE} = 5V, I_C = 0.1A$ $V_{CE} = 5V, I_C = 1A$	20 8		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 1A, I_B = 0.2A$		1	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 1A, I_B = 0.2A$		1.5	V
t_{ON}	Turn ON Time	$V_{CC} = 200V, I_C = 0.8A$		1	μs
t_{STG}	Storage Time	$I_{B1} = -I_{B2} = 0.08A$		2.5	μs
t_F	Fall Time	$R_L = 250\Omega$		1	μs

Typical Characteristics

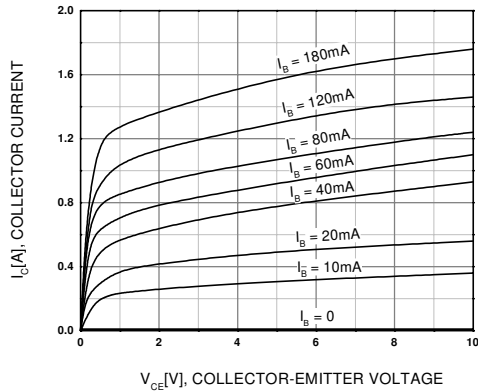


Figure 1. Static Characteristic

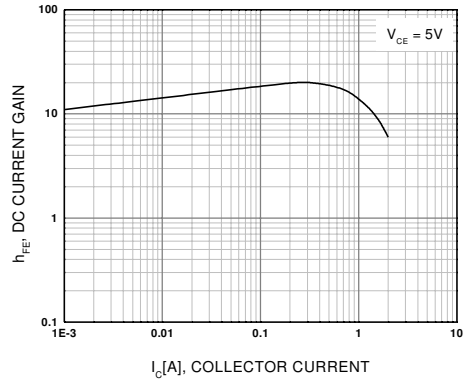


Figure 2. DC current Gain

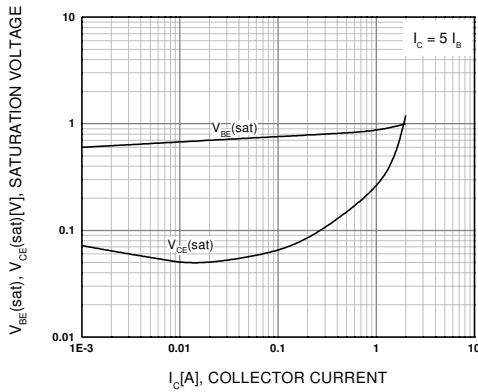


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

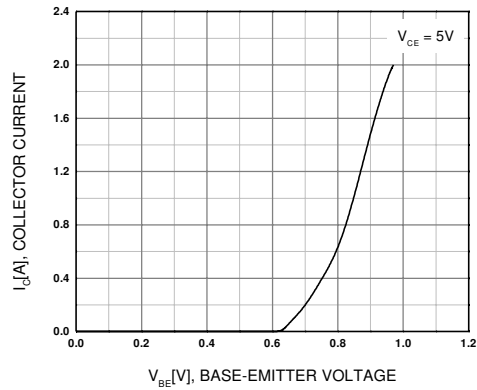


Figure 4. Base-Emitter on Voltage

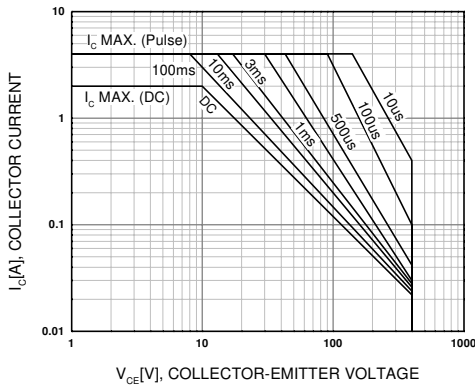


Figure 5. Safe Operating Area

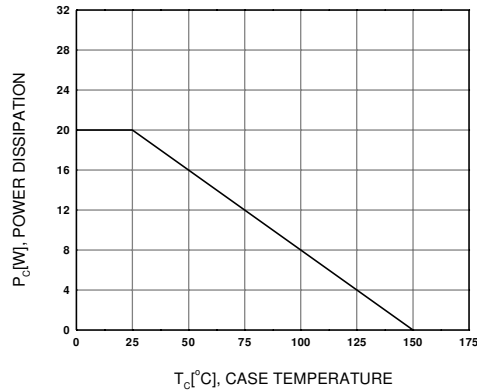
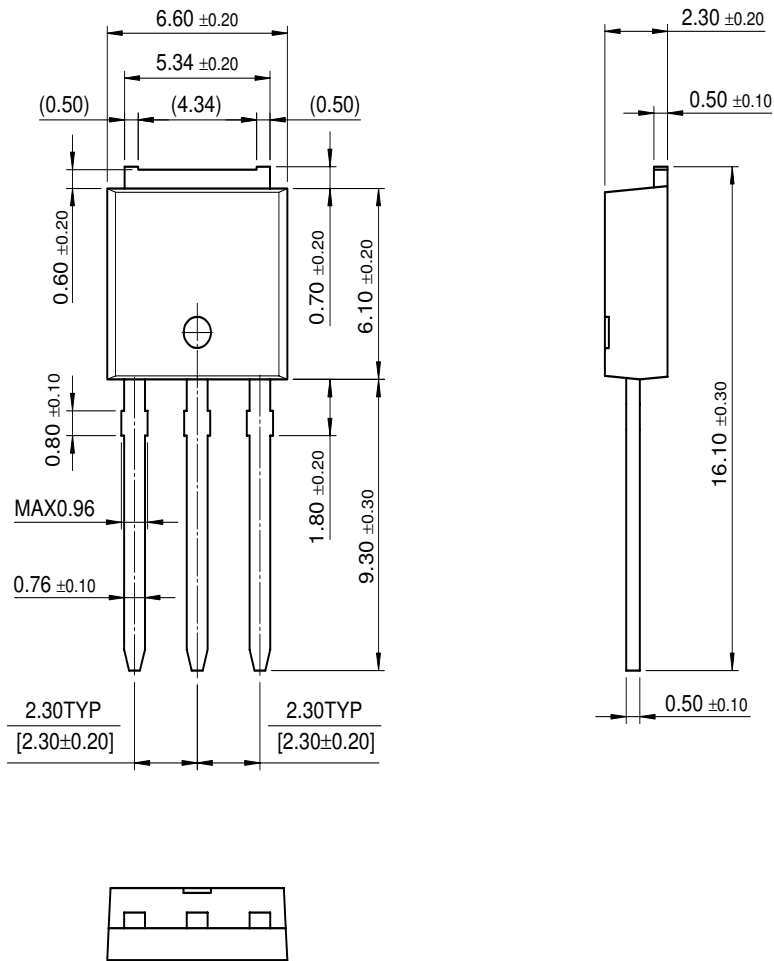


Figure 6. Power Derating

Package Dimensions

I-PAK



Dimensions in Millimeters

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